

Corrections on “Improvement of Third-Order Intermodulation Product of RF and Microwave Amplifiers by Injection”

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In the above paper,¹ Fig. 12(b) appears incorrectly. The correct figure depicting the output spectrum of the heterojunction bipolar transistor (HBT) power amplifier at 28-dBm output power after applying the second harmonic technique is as shown here in Fig. 1.

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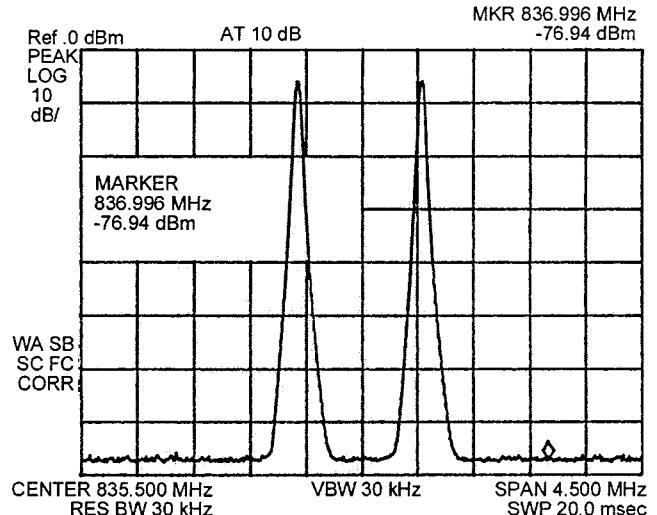


Fig. 1. Output spectrum of the HBT power amplifier at 28-dBm output after applying the second harmonic technique.